L Number	Hits	Search Text	DB	Time stamp
1	57	chalcogenide adj glass and (non-volatile	USPAT;	2004/06/12 14:23
		nonvolatile) near2 memory	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
2	45		USPAT;	2004/06/12 14:25
		nonvolatile) near2 memory and method.clm.	US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
3	6	chalcogenide adj glass.ti,ab,clm. and	USPAT;	2004/06/12 14:27
]	J	(non-volatile nonvolatile) near2	US-PGPUB;	
		memory.ti,ab,clm. and method.clm.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
4	3715		USPAT;	2004/06/12 14:29
		(257/299) or (257/300) or (257/63) or	US-PGPUB	
		(257/52) or (257/55) or (257/2) or		
_		(501/11) or (501/19) or (501/42)).CCLS.		0004/06/10 14:00
5	8	(((257/296) or (257/297) or (257/298) or (257/299) or (257/300) or (257/63) or	USPAT;	2004/06/12 14:29
		(257/299) or (257/300) or (257/63) or (257/52) or (257/55) or (257/2) or	US-PGPUB; EPO; JPO;	
		(501/11) or (501/19) or (501/42)).CCLS.)	DERWENT;	
		and germanium and selenide and (silver ag)	IBM TDB	
		and (non-volatile nonvolatile) near2		
		memory		
-	0	("chalcogenide adj glass.clm. and	USPAT;	2004/06/11 14:58
		chalcogenide.ti.").PN.	US-PGPUB;	
			EPO; JPO;	i
			DERWENT;	
	0.4	.h.1	IBM_TDB USPAT;	2002/09/17 10:05
_	24	chalcogenide adj glass.clm. and chalcogenide.ti.	US-PGPUB;	2002/09/17 10:05
		Charcogenide.ci.	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	3	pcram.ti.	USPAT;	2002/09/17 10:06
:			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	2002/09/17 10:07
-	0	pcram.ti,ab,clm. and processor.clm.	USPAT; US-PGPUB;	2002/09/17 10:07
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	1285	ram near3 processor.ti,ab.	USPĀT;	2002/09/17 10:07
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	209	ram near? proceeds ti	IBM_TDB USPAT;	2002/09/17 10:07
-	209	ram near3 processor.ti.	US-PGPUB;	2002/03/1/ 10:0/
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	5	ram near3 processor.ti. and processor.clm.	USPAT;	2002/09/17 10:24
		•	US-PGPUB;	
]			EPO; JPO;	
			DERWENT;	
	2.5		IBM_TDB	2002/00/17 10 25
-	36	chalcogenide near4 use	USPAT;	2002/09/17 10:26
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
				·

-	0	chalcolgenide near6 (dop\$3 or impurit\$3)	USPAT;	2002/12/19 14:29
		near6 (metal or silver or ag or copper or	US-PGPUB;	
		cu or platinum or pt or gold or au or	EPO; JPO;	
		cadmium or cd or ruthenium or ru or coablt	DERWENT;	
		or co or zinc or zn or chromium or cr or	IBM_TDB	
		manganese or mn or nickel or ni) and		
		memory adj2 (cell or device).ti,ab,clm.		
-	0	chalcolgenide adj glass near12 (metal or	USPAT;	2002/12/16 15:51
		silver or ag or copper or cu or platinum	US-PGPUB;	
		or pt or gold or au or cadmium or cd or	EPO; JPO;	
		ruthenium or ru or cobalt or co or zinc or	DERWENT;	
		zn or chromium or cr or manganese or mn or	IBM TDB	
		nickel or ni) and memory adj2 (cell or	_	
		device).ti,ab,clm.		
l _	0	chalcolgenide adj glass and (metal or	USPAT;	2002/12/16 15:51
Ì		silver or ag or copper or cu or platinum	US-PGPUB;	
		or pt or gold or au or cadmium or cd or	EPO; JPO;	
		ruthenium or ru or cobalt or co or zinc or	DERWENT;	
		zn or chromium or cr or manganese or mn or	IBM TDB	
			100-100	
		nickel or ni) and memory adj2 (cell or		
1		device).ti,ab,clm.	HCDATT.	2002/12/16 16:33
-	3	chalcogenide adj glass near12 (metal or	USPAT;	2002/12/10 10:33
		silver or ag or copper or cu or platinum	US-PGPUB;	
		or pt or gold or au or cadmium or cd or	EPO; JPO;	
		ruthenium or ru or cobalt or co or zinc or	DERWENT;	
		zn or chromium or cr or manganese or mn or	IBM_TDB	
		nickel or ni) and memory adj2 (cell or		
		device).ti,ab,clm.		
-	21		USPAT;	2002/12/16 16:36
		silver or ag or copper or cu or platinum	US-PGPUB;	
1		or pt or gold or au or cadmium or cd or	EPO; JPO;	
		ruthenium or ru or cobalt or co or zinc or	DERWENT;	
		zn or chromium or cr or manganese or mn or	IBM_TDB	
		nickel or ni) and 257/\$6.ccls.	_	
-	115	(365/153).CCLS.	USPAT;	2002/12/17 15:34
			US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
1			IBM_TDB	
-	6	((365/153).CCLS.) and chalcogenide	USPĀT;	2002/12/17 15:51
1			US-PGPUB;	
1			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	2	ag adj content and chalcogenide and memory	USPAT;	2002/12/17 16:03
		-	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	ag adj content and "ag-ge-te" and memory	USPAT;	2002/12/17 16:06
	1		US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
_	45	chalcogenide adj glass and (silver or ag)	USPAT;	2002/12/17 16:07
		and memory	US-PGPUB;	,,
			EPO; JPO;	
			DERWENT;	
l			IBM TDB	
_	3	chalcogenide adj glass and (silver or ag)	USPAT;	2002/12/17 16:39
l	1	near4 (content or concentration) and	US-PGPUB;	2002/12/17 10.39
		memory	EPO; JPO;	
		memor y	DERWENT;	
Ì			IBM TDB	
_	7	(Hg_2010129_6 or Hg_5470202 6 or		2002/12/12 16.41
-	'	,	USPAT;	2002/12/17 16:41
		US-6084796-\$ or US-6487106-\$ or	US-PGPUB	
	1	US-3827033-\$ or US-3721838-\$).did. or		
		(US-20020168820-\$).did.	HODAM.	2002/10/17 16 10
_	0	j	USPAT;	2002/12/17 16:43
]		(percentage or concentration or content)	US-PGPUB	0000/10/15 15 11
_	0	"ge se.sub.3" and (silver or ag) near6	USPAT;	2002/12/17 16:44
l		(percentage or concentration or content)	US-PGPUB	

-	0	"ge se.sub."\$1 and (silver or ag) near6	EPO; JPO;	2002/12/17 16:50
		(percentage or concentration or content)	DERWENT; IBM TDB	
_	1	("6487106").PN.	USPĀT;	2002/12/18 16:09
			US-PGPUB; EPO; JPO;	
			DERWENT;	}
_	2	(percent or percentage) near4 (silver or	IBM_TDB USPAT;	2002/12/18 17:48
	-	ag) and chalcogenide adj glass and memory	US-PGPUB;	2002/12/10 1/110
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	119	(tie adj line or tie-line) and phase adj	USPAT; US-PGPUB;	2002/12/19 10:35
			EPO; JPO;	
			DERWENT; IBM TDB	
-	9	(0-0)	USPAT;	2002/12/19 11:07
		phase adj diagram	US-PGPUB; EPO; JPO;	
			DERWENT;	
_	0	("kozicki.in.").PN.	IBM_TDB USPAT;	2002/12/19 11:07
			US-PGPUB; EPO; JPO;	
			DERWENT;	
_	39	kozicki.in.	IBM_TDB USPAT;	2002/12/19 11:12
	. 33	NOZICKI:III.	US-PGPUB;	2002/12/13 11:12
			EPO; JPO; DERWENT;	
	_		IBM_TDB	
-	5	(("5761115") or ("5896312") or ("5914893") or ("6084796")).PN.	USPAT; US-PGPUB;	2002/12/19 11:15
		, , ,	EPO; JPO;	
			DERWENT; IBM ·TDB	
- '	1	("6469364").PN.	USPĀT; US-PGPUB;	2002/12/19 11:15
			EPO; JPO;	
			DERWENT; IBM TDB	
-	18	(US-6084796-\$ or US-6487106-\$ or	USPAT;	2002/12/19 11:16
		US-3721838-\$ or US-3810128-\$ or US-3827033-\$ or US-6418049-\$ or	US-PGPUB; DERWENT	
		US-5479382-\$ or US-6469364-\$ or		
		US-6388324-\$ or US-5914893-\$ or US-5896312-\$ or US-5761115-\$ or		
		US-5500532-\$ or US-5314772-\$).did. or (US-20020000666-\$ or US-20020190350-\$ or		
		US-20020168820-\$).did. or		
_	2	(US-5761115-\$).did. ("6348365").PN.	USPAT;	2002/12/19 12:02
		(0010000).In.	US-PGPUB;	2002/12/19 12:02
			EPO; JPO; DERWENT;	
		(H.C.) 100 (0H) - 717	IBM_TDB	
-	2	("6418049").PN.	USPAT; US-PGPUB;	2002/12/19 12:02
			EPO; JPO;	
			DERWENT; IBM TDB	
-	0	switching adj field and chalcogenide adj glass and memory and ("Ag-Ge-Se" or	USPĀT; US-PGPUB;	2002/12/19 14:31
		(silver or ag) near3 (percent or	EPO; JPO;	
		percentage))	DERWENT; IBM TDB	
			TDEI_TDD	

_	7	switching adj field and chalcogenide adj	USPAT; US-PGPUB;	2002/12/19 15:38
		grade and memory	EPO; JPO;	
			DERWENT;	
	_	suitabing add amond and abalassanide add	IBM_TDB	2002/12/19 15:41
_	4	switching adj speed and chalcogenide adj glass and memory and (silver or ag)	USPAT; US-PGPUB;	2002/12/19 15:41
		grass and memory and (sirver or ag)	EPO; JPO;	
	11		DERWENT;	
1			IBM_TDB	
-	36	switching and chalcogenide adj glass and	USPAT; US-PGPUB;	2002/12/19 16:59
		memory and (silver or ag)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	16042	non-volatile adj memory.ti,ab.,clm. and	USPAT;	2002/12/19 17:02
		(germanium adj selenide or "ge.sub.x se.sub.1-x" or "Ag-Ge-Se" or (silver or	US-PGPUB; EPO; JPO;	
		ag) near6 chalcogenide)	DERWENT;	
			IBM_TDB	
-	16042	non-volatile adj memory.ti,ab.,clm. and	USPAT;	2002/12/19 17:06
		(germanium adj selenide or "ge.sub.x	US-PGPUB;	
	1	se.sub.1-x" or "Ag-Ge-Se" or ((silver or ag) near6 chalcogenide))	EPO; JPO; DERWENT;	
			IBM TDB	
-	16042	non-volatile adj memory.ti,ab.,clm. and	USPAT;	2002/12/19 17:07
		(germanium adj selenide or "ge.sub.x	US-PGPUB;	
		se.sub.1-x" or "Ag-Ge-Se" or (silver or ag) near6 chalcogenide)	EPO; JPO; DERWENT;	
		agy heard charcogeniue)	IBM TDB	·
_	1	non-volatile adj memory.ti,ab,clm. and	USPAT;	2002/12/19 18:22
	İ	(germanium adj selenide or "ge.sub.x	US-PGPUB;	
		se.sub.1-x" or "Ag-Ge-Se" or (silver or	EPO; JPO;	
		ag) near6 chalcogenide)	DERWENT; IBM TDB	
_	231	(dendrite or dendritic) near12 voltage or	USPAT;	2002/12/19 18:24
		electric adj field near12 chalcogenide adj	US-PGPUB;	
		glass	EPO; JPO;	
			DERWENT; IBM TDB	
_	157	(dendrite or dendritic) near6 voltage or	USPAT;	2002/12/19 18:24
		electric adj field near6 chalcogenide adj	US-PGPUB;	
		glass	EPO; JPO;	
			DERWENT; IBM TDB	
_	0	(dendrite or dendritic) near6 (voltage or	USPAT;	2002/12/19 18:25
		electric adj field) near6 chalcogenide adj	US-PGPUB;	
1		glass	EPO; JPO;	
1	[DERWENT; IBM TDB	
_	0	 (dendrite or dendritic) near12 (voltage or	USPAT;	2002/12/19 18:25
		electric adj field) near12 chalcogenide	US-PGPUB;	
		adj glass	EPO; JPO;	
			DERWENT; IBM TDB	
_	3	 (dendrite or dendritic) near12 (voltage or	USPAT;	2002/12/19 18:33
		electric adj field) and chalcogenide adj	US-PGPUB;	
		glass.ti,ab.	EPO; JPO;	
			DERWENT;	
_	n	("t.sub.g" ot transition adj temperature)	IBM_TDB USPAT;	2002/12/19 18:35
	ļ	near12 chalcogenide adj glass and	US-PGPUB;	
		photodiffusion	EPO; JPO;	
			DERWENT;	
_	ا م ا	("t.sub.g" or transition adj temperature)	IBM_TDB USPAT;	2002/12/19 18:36
]	near12 chalcogenide adj glass and	US-PGPUB;	
		photodiffusion	EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	0	("t.sub.g" or temperature) near12	USPAT;	2002/12/19 18:36
]	chalcogenide adj glass and photodiffusion	US-PGPUB;	
į			EPO; JPO;	
	1		DERWENT;	
		(## aub all au tompomotume) monm12	IBM_TDB USPAT;	2002/12/19 18:41
-	50	("t.sub.g" or temperature) near12	US-PGPUB;	2002/12/19 18:41
		chalcogenide adj glass	EPO; JPO;	
			DERWENT;	
			IBM TDB	
l _	0	photodissolution near12 chalcogenide	USPAT;	2002/12/19 18:42
		near12 silver	US-PGPUB;	2002, 12, 13 10.12
}			EPO; JPO;	i
			DERWENT;	
			IBM TDB	
_	3	photodissolution near12 silver	USPAT;	2002/12/19 18:42
ĺ		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	microelectronic adj programmable adj	USPAT;	2002/12/20 15:39
		device and processor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0000/10/00 16 07
-	3	pcram and processor .	USPAT;	2002/12/20 16:27
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
l _	799	campbell.in. and memory	USPAT;	2002/12/20 16:27
	, , , ,	campbell: In: and memory	US-PGPUB;	2002/12/20 10:2/
1			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	7	PCRAM.ti,ab.	USPĀT;	2002/12/20 16:42
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	4867	(programmable adj2 device or PCRAM).ti,ab.	USPAT;	2002/12/20 16:43
			US-PGPUB;	
1			EPO; JPO;	
			DERWENT; IBM TDB	
_	214	 (programmable adj memory adj device or	USPAT;	2002/12/20 16:44
	214	PCRAM).ti,ab.	US-PGPUB;	2002/12/20 10.44
		1 0111111111111111111111111111111111111	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	(programmable adj memory adj device or	USPAT;	2002/12/20 18:18
		PCRAM).ti,ab. and chalcogenide adj glass	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	kristy.in. and campbell.in. and	USPAT;	2002/12/20 18:19
		chalcogenide	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	0	kriety in and compholi in	IBM_TDB USPAT;	2002/12/20 18:19
-		kristy.in. and campbell.in.	US-PGPUB;	2002/12/20 10:19
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	campbell.in. and chalcogenide	USPAT;	2002/12/20 18:20
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	<u> </u>

-	1	("ge.sub.x se.sub.1-x" or "ge.sub.y.	USPAT;	2002/12/20 18:28
		se.sub.1-y" or "ag-ge-se") and glass and	US-PGPUB;	
		(silver or ag) and memory	EPO; JPO;	
	İ		DERWENT;	
		(Non-sub-u-sub-1 ull an Use sub-u-	IBM_TDB	2002/12/20 18:52
-	2	("ge.sub.x se.sub.1-x" or "ge.sub.y.	USPAT;	2002/12/20 18:52
	1	se.sub.1-y" or "ag-ge-se" or "ge.sub.3	US-PGPUB;	
		se.sub.7") and glass and (silver or ag)	EPO; JPO;	
		and memory	DERWENT; IBM TDB	
	۱ ,	/llan sub w on sub 1 wll on llan sub w	USPAT;	2002/12/20 18:57
-	4	("ge.sub.x se.sub.1-x" or "ge.sub.y. se.sub.1-y" or "ag-ge-se" or	US-PGPUB;	2002/12/20 18.3/
		"ge.sub."?"se.sub."?) and glass and	EPO; JPO;	
	i	(silver or ag) and memory	DERWENT;	
		(Silver or ag, and memory	IBM TDB	
_)	("5761115").PN.	USPAT;	2002/12/20 20:47
	-	(3/01113).111.	US-PGPUB;	2002/12/20 20.47
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	27	chalcogenide adj glass near5	USPAT;	2002/12/20 20:48
	1	oxide.ti,ab,clm.	US-PGPUB;	2002, 12, 20 20:10
	1		EPO; JPO;	
	İ		DERWENT;	
			IBM TDB	
	0	chalcogenide adj glass near5	USPAT;	2002/12/20 20:49
		oxide.ti,ab,clm. and memory.ti,ab,clm.	US-PGPUB;	
		1	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	chalcogenide adj glass near5	USPAT;	2002/12/20 20:49
	ļ	oxide.ti,ab,clm. and storage.ti,ab,clm.	US-PGPUB;	
	j		EPO; JPO;	;
			DERWENT;	
			IBM_TDB	
-	692		USPAT;	2002/12/21 11:59
		(257/63) or (257/298)).CCLS.	US-PGPUB	
-	11		USPAT;	2002/12/21 12:00
		(257/63) or (257/298)).CCLS.) and	US-PGPUB;	
		chalcogenide adj glass and memory	EPO; JPO;	<u>l</u>
			DERWENT;	
	5	(((257/2) or (257/52) or (257/55) or	IBM_TDB USPAT;	2002/12/21 12:01
-]	((257/2) of (257/32) of (257/33) of (257/63) or (257/298)).CCLS.) and	US-PGPUB;	2002/12/21 12:01
		chalcogenide adj glass and	EPO; JPO;	
		memory.ti,ab,clm.	DERWENT;	
			IBM TDB	
_	95	(365/163).CCLS.	USPAT;	2002/12/21 12:01
			US-PGPUB;	
			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	57	((365/163).CCLS.) and chalcogenide	USPĀT;	2002/12/21 12:01
		_	US-PGPUB;	
			EPO; JPO;	
	}		DERWENT;]
			IBM_TDB	
-	59	((((257/2) or (257/52) or (257/55) or	USPAT;	2002/12/21 12:03
		(257/63) or (257/298)).CCLS.) and	US-PGPUB;	
		chalcogenide adj glass and	EPO; JPO;	
		memory.ti,ab,clm.) or (((365/163).CCLS.)	DERWENT;	
		and chalcogenide)	IBM_TDB	2002/10/01 10 01
-	5		USPAT;	2002/12/21 12:04
		(257/63) or (257/298)).CCLS.) and	US-PGPUB;	
		chalcogenide adj glass and memory.ti,ab,clm.) or (((365/163).CCLS.)	EPO; JPO;	
		and chalcogenide)) and silver	DERWENT; IBM TDB	
		and charcogenide)) and Silver	קח ד הוסד	

				10000 /10 /05 10 50
_	31		USPAT;	2002/12/21 12:59
		US-5166758-\$ or US-6487113-\$ or	US-PGPUB;	
		US-6462984-\$ or US-5072423-\$ or	JPO; DERWENT	
		US-5272667-\$ or US-5363329-\$ or US-5406509-\$ or US-5314772-\$ or	DEKWENI	ļ
		US-6487106-\$ or US-6469364-\$ or		
		US-3721838-\$ or US-3810128-\$ or		1
	ļ	US-3827033-\$ or US-6348365-\$ or		
		US-6084796-\$ or US-5914893-\$ or		
		US-5896312-\$ or US-5479382-\$ or		
		US-6418049-\$ or US-5761115-\$ or		
		US-6388324-\$ or US-5500532-\$).did. or		
		(US-20020000666-\$ or US-20020190350-\$ or		
		US-20020168820-\$).did. or		ŀ
		(JP-03044703-\$).did. or (US-5761115-\$ or		
		US-6348365-\$ or EP-846353-\$).did.		
-	13		USPAT;	2003/11/23 11:29
		"ge.sub."??"Se.sub."\$5	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	4.00	501/11	IBM_TDB	0000/11/00 15:40
_	193		USPAT	2003/11/23 15:40
-	199	501/11	USPAT; US-PGPUB	2003/11/23 15:40
_	279	501/19	US-PGPUB USPAT;	2003/11/23 15:40
-	2/9	501/19	US-PGPUB	2003/11/23 13:40
_	192	501/42	USPAT;	2003/11/23 15:40
	1 92	001, 12	US-PGPUB	-555, 11, 25 15.40
_	0	501/11 and 501/19 and 501/42	USPAT;	2003/11/23 15:40
			US-PGPUB	
_	3	501/19 and 501/42	USPAT;	2003/11/23 15:57
			US-PGPUB	
-	8	germanium and selenium and chalcogenide	USPAT;	2003/11/23 16:42
		and silver and phase adj transition	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	
-	1	JP-03044703\$-\$.DID.	USPAT;	2003/11/23 16:57
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	<u> </u>
_	14	(("6388324") or ("20020000666") or	USPAT;	2004/06/11 13:24
	14	("5500532") or ("6418049") or ("5751012")	US-PGPUB	2004/00/11 13.24
		or ("5789277") or ("6348365") or		
		("20020168820") or ("6469364") or		
		("6348365") or ("6418049") or ("5761115")		
		or ("5896312") or ("5914893") or		
		("6084796") or ("6635914")).PN.	-	
-	3	((("6388324") or ("20020000666") or	USPAT;	2004/06/10 18:35
		("5500532") or ("6418049") or ("5751012")	US-PGPUB;	
		or ("5789277") or ("6348365") or	EPO; JPO;	
		("20020168820") or ("6469364") or	DERWENT;	
		("6348365") or ("6418049") or ("5761115")	IBM_TDB	
ļ		or ("5896312") or ("5914893") or		
		("6084796") or ("6635914")).PN.) and		
	_	\$6"Ge.sub."\$6	HCDATT.	2004/06/10 10:35
-	2	, , , , , , , , , , , , , , , , , , , ,	USPAT;	2004/06/10 18:35
		("5500532") or ("6418049") or ("5751012") or ("5789277") or ("6348365") or	US-PGPUB; EPO; JPO;]
		("20020168820") or ("6348363") or	DERWENT;	
		("6348365") or ("6418049") or ("5761115")	IBM TDB	
		or ("5896312") or ("5914893") or]
		("6084796") or ("6635914")).PN.) and]	
		\$6"Ge.sub."\$6 near6 (glass amorphous)		
-	2	("6487106").PN.	USPAT;	2004/06/11 10:31
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

	_		~~~	
-	2	("5761115").PN.	USPAT;	2004/06/11 11:22
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	13		USPAT;	2004/06/11 11:34
		memory adj cell and (non-volatile	US-PGPUB;	
	1	nonvolatile)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	13	chalcogenide adj glass and "Ge.sub."\$6 and	USPAT;	2004/06/11 11:35
		memory adj cell and (non-volatile	US-PGPUB;	
		nonvolatile) and (silver Ag)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	13		USPAT;	2004/06/11 11:40
		memory adj cell and (non-volatile	US-PGPUB;	
		nonvolatile) and (silver Ag) and	EPO; JPO;	
		(semiconductor semiconducting)	DERWENT;	
			IBM TDB	
-	24	(semiconductor semiconducting) near4	USPĀT;	2004/06/11 11:41
		(glass glasses) and "Ge.sub."\$9 and	US-PGPUB;	
		(non-volatile non-volatile)	EPO; JPO;	
			DERWENT;	•
			IBM TDB	
-	20	(semiconductor semiconducting) near2	USPAT;	2004/06/11 11:42
		(glass glasses) and "Ge.sub."\$9 and	US-PGPUB;	
,		(non-volatile non-volatile)	EPO; JPO;	
		(DERWENT;	
İ			IBM TDB	
_	20	(semiconductor semiconducting) near2	USPAT;	2004/06/11 11:42
		(glass glasses) and "Ge.sub."\$9 and	US-PGPUB;	
		(non-volatile non-volatile) and memory	EPO; JPO;	
		(,	DERWENT;	
			IBM TDB	
_	8	(semiconductor semiconducting) near2	USPAT;	2004/06/11 11:42
		(glass glasses) and "Ge.sub."\$9 and	US-PGPUB;	
		(non-volatile non-volatile) and memory and	EPO; JPO;	
-		\$6"Se.sub."\$3	DERWENT;	
			IBM TDB	
-	14	(US-5914893-\$ or US-5896312-\$ or	USPAT;	2004/06/11 13:25
		US-5789277-\$ or US-6635914-\$ or	US-PGPUB	}
		US-5500532-\$ or US-6469364-\$ or		
		US-5751012-\$ or US-5761115-\$ or		
		US-6388324-\$ or US-6418049-\$ or		
		US-6348365-\$ or US-6084796-\$).did. or		
		(US-20020000666-\$ or		
		US-20020168820-\$).did.		
-	0	wo-0221542\$-\$.did.	USPAT;	2004/06/11 13:25
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1	wo-200221542\$-\$.did.	USPAT;	2004/06/11 13:26
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1	wo-200048196\$-\$.did.	USPAT;	2004/06/11 13:27
			US-PGPUB;	
			EPO; JPO;	
	İ		DERWENT;	
			IBM TDB	
_	0	wo-199748032\$-\$.did.	USPAT;	2004/06/11 13:27
	١ ١	· · · · · · · · · · · · · · · · · · ·	US-PGPUB;	
			EPO; JPO;	
ļ İ	İ		DERWENT;	
			IBM TDB	

				T
-	1	wo-9748032\$-\$.did.	USPAT; US-PGPUB;	2004/06/11 13:28
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	wo-9928914\$-\$.did.	USPAT;	2004/06/11 13:28
			US-PGPUB;	
			EPO; JPO; DERWENT;	l i
			IBM TDB	
_	0	"Ge.sub.x Se.sub.1-x"\$6 and silver and	USPAT;	2004/06/11 15:00
		chalcogenide adj glass and (semiconductor	US-PGPUB;	
		semiconducting) and memory	EPO; JPO;	
			DERWENT;	
	27	"Ge.sub.x"\$8 and silver and chalcogenide	IBM_TDB USPAT;	2004/06/11 18:36
_	2'	adj glass and (semiconductor	US-PGPUB;	2004/00/11 10:30
		semiconducting) and memory	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	18	kozicki.in. and "0.5"	USPAT;	2004/06/11 18:36
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	11	kozicki.in. and "0.5" and "0.1"	USPAT;	2004/06/11 18:40
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	9	kozicki.in. and "0.5" same "0.1"	IBM_TDB USPAT;	2004/06/12 12:28
İ		ACTIONITIES AND U.S SAME U.I	US-PGPUB;	2004,00,12 12.20
			EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	0004/05/55 55 55
_	9	(mitkova.in. kozicki.in.) and "0.5" same	USPAT; US-PGPUB;	2004/06/11 19:28
		V.1	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	20	(mitkova.in. kozicki.in.) and ("0.4" "0.5"	USPAT;	2004/06/11 19:29
		"0.6")	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	9	(mitkova.in. kozicki.in.) and ("0.4" "0.5"	USPAT;	2004/06/11 19:29
		"0.6") same x	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	1	 jp-03044703\$-\$.did.	IBM_TDB USPAT;	2004/06/12 12:30
		1000111004 A.GTG.	US-PGPUB;	2007/00/12 12:30
		•	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	818		USPAT;	2004/06/12 12:31
		memory adj cell and ("same chip" "single chip")	US-PGPUB; EPO; JPO;	
		Chip /	DERWENT;	
			IBM TDB	
-	53	integrated adj circuit same processor same	USPĀT;	2004/06/12 13:04
		memory adj cell and ("same chip" "single	US-PGPUB;	
		chip")	EPO; JPO;	
			DERWENT; IBM TDB	
_	18	integrated adj circuit same processor same	USPAT;	2004/06/12 13:11
		memory adj cell same ("same chip" "single	US-PGPUB;	
		chip")	EPO; JPO;	
			DERWENT;	
			IBM TDB	

-	0	integrated adj circuit same processor same	USPAT;	2004/06/12 13:11
		memory adj cell same ("same chip" "single chip") same (non-volatile nonvolatile)	US-PGPUB; EPO; JPO; DERWENT; IBM TDB	
-	0	(IC integrated adj circuit) same processor same memory adj cell same ("same chip" "single chip") same (non-volatile nonvolatile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/06/12 14:22